



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected Up To 2KV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: TSSOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.039 grams (approximate)



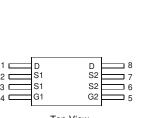


ESD PROTECTED TO 2kV

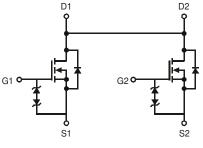
TOP VIEW



BOTTOM VIEW







Internal Schematic

### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 3)	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	١ <sub>D</sub>	8.58 5.73	А
Pulsed Drain Current (Note 4)			I <sub>DM</sub>	36	А

TSSOP-8L

#### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	0.88	w
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 3)	R <sub>0JA</sub>	141.57	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

Notes: 1. No purposefully added lead.

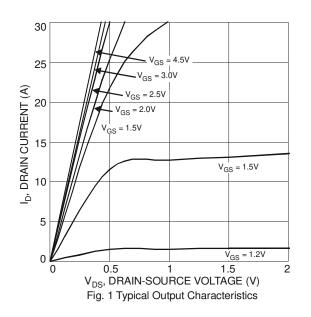
Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
Device mounted on FR-4 PCB, with minimum recommended pad layout.

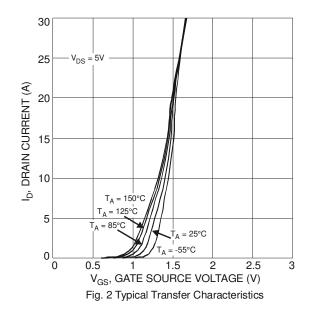
4. Repetitive rating, pulse width limited by junction temperature.



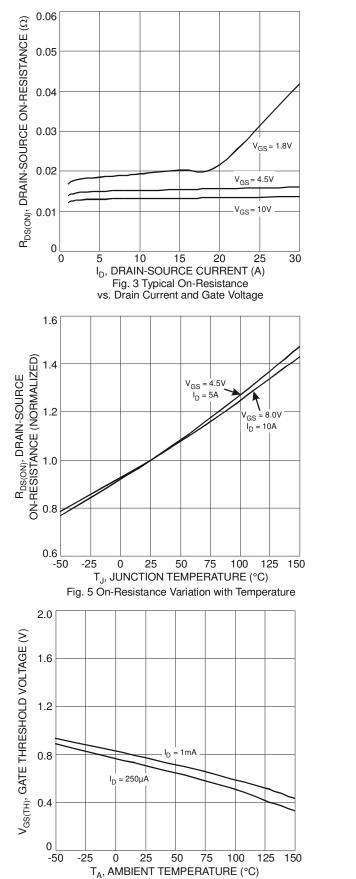
Electrical Characteristics @T <sub>A</sub> = 25°C unless otherwise specified							
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)		-					
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.4	0.72	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	11 13	14.5 16.5	mΩ	$V_{GS} = 4.5V, I_D = 9.4A$ $V_{GS} = 2.5V, I_D = 8.3A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	19	-	S	$V_{DS} = 5V, I_D = 9.4A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.65	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.3A	
DYNAMIC CHARACTERISTICS (Note 6)						÷	
Input Capacitance	Ciss	-	1495	-	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	161	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	152	-	pF		
Gate Resistance	Rg	-	1.42	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	-	16.5	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	2.5	-	nC	$-V_{GS} = 4.5V, V_{DS} = 10V,$ $-I_{D} = 9.4A$	
Gate-Drain Charge	Q <sub>gd</sub>	-	3.2	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	10.39	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_{GEN} = 6\Omega, I_D = 1A, R_1 = 10\Omega$	
Turn-On Rise Time	tr	-	11.66	-	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	59.38	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	16.27	-	ns	7	

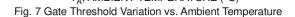
5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to production testing. Notes:

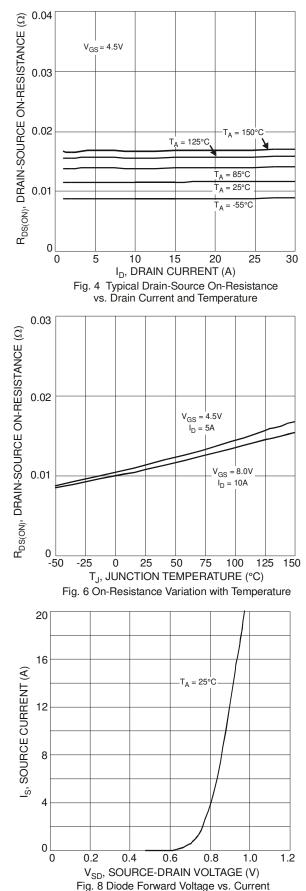






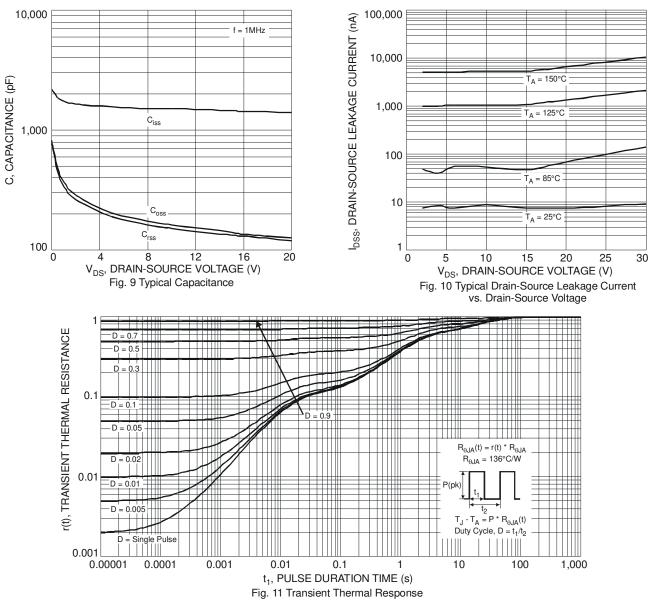








## DMN2016UTS

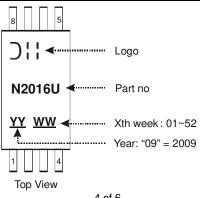


### Ordering Information (Note 7)

Part Number	Case	Packaging
DMN2016UTS-13	TSSOP-8L	2500 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**





Тур

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0.925

3.025

0.65

6.40

4.50 4.425

1.20

0.15

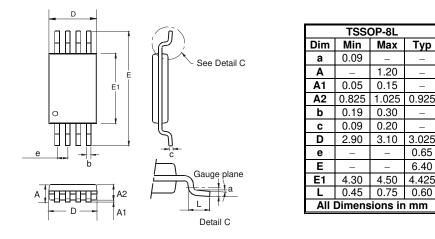
1.025

0.30

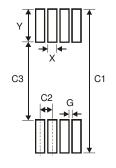
0.20

3.10

### **Package Outline Dimensions**



# Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20



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